

N-Ch MOSFET

General Description

The WSR170N04G uses SGT and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

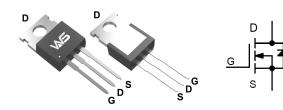
Product Summery

BVDSS	RDSON	ID
40V	3mΩ	170A

Application

- Load switch
- Battery protection
- Uninterruptible power supply

TO-220AB Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	40	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	170	Α	
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ 10V ¹	135	Α	
I _{DM}	Pulsed Drain Current ² 800		Α	
EAS	Single Pulse Avalanche Energy ³	450	mJ	
P _D @T _C =25℃	Total Power Dissipation ⁴ 185		W	
T _J T _{STG}	Operating Junction Temperature Range	-55 to 150	$^{\circ}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		50	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		0.7	°C/W

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Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.057		V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =20A		1.9	3	mΩ
V _{GS(th)}	Gate Threshold Voltage	V V 1 050 A	1.2	1.8	2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-5.68		mV/℃
l	Drain-Source Leakage Current	V_{DS} =40V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	uA
I _{DSS}		V_{DS} =40V , V_{GS} =0V , T_{J} =55 $^{\circ}$ C			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20 V$, V_{DS} = $0 V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =15A		50		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.0		Ω
Q_{g}	Total Gate Charge (4.5V)			45		
Q _{gs}	Gate-Source Charge	V _{DS} =20V , V _{GS} =10V , I _D =20A		12		nC
Q _{gd}	Gate-Drain Charge			18		
$T_{d(on)}$	Turn-On Delay Time	V_{DS} =20V , V_{GS} =10V , I_{D} =20A , Rg =1 Ω .		19		
Tr	Rise Time			10		20
T _{d(off)}	Turn-Off Delay Time			59		ns
T _f	Fall Time			32		
Ciss	Input Capacitance	V _{DS} =20V , V _{GS} =0V , f=1MHz		3950		
C _{oss}	Output Capacitance			1120		pF
C _{rss}	Reverse Transfer Capacitance			98		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			170	Α
I _{SM}	Pulsed Source Current ^{2,6}				800	Α
V_{SD}	Diode Forward Voltage ²	V_{GS} =0 V , I_{S} =1 A , T_{J} =25 $^{\circ}$ \mathbb{C}			1.2	٧
t _{rr}	Reverse Recovery Time	IF=20A ,dI/dt=100A/μs,TJ=25 C		35		nS
Q _{rr}	Reverse Recovery Charge			56		nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25 Ω



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Typical Characteristics

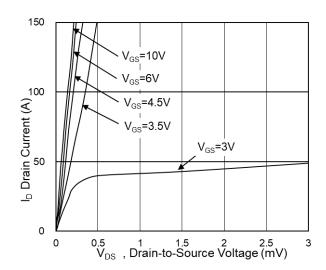


Fig.1 Typical Output Characteristics

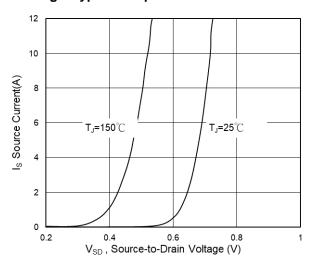


Fig.3 Source Drain Forward Characteristics

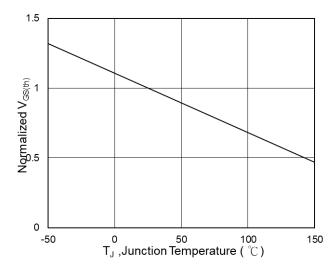


Fig.5 Normalized V_{GS(th)} vs T_J

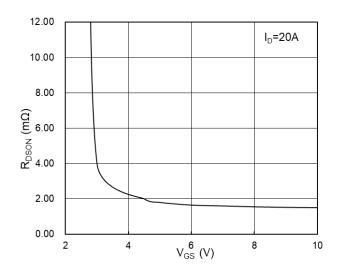


Fig.2 On-Resistance vs G-S Voltage

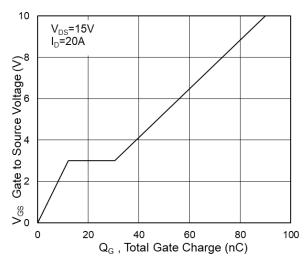


Fig.4 Gate-Charge Characteristics

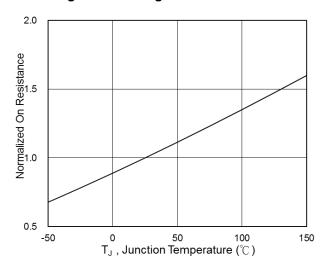


Fig.6 Normalized R_{DSON} vs T_J





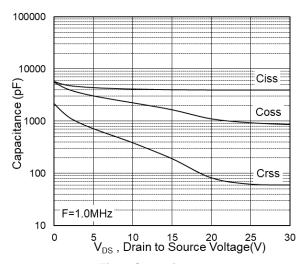


Fig.7 Capacitance

Fig.8 Safe Operating Area

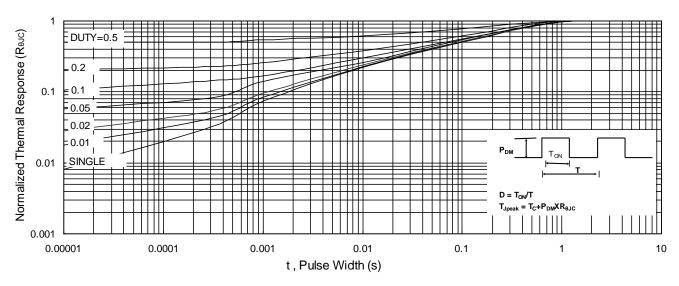
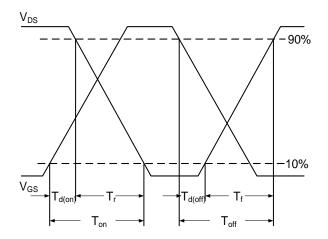


Fig.9 Normalized Maximum Transient Thermal Impedance



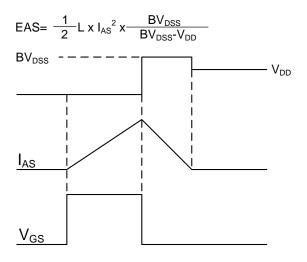


Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform



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